

United States Patent and Trademark Office



UNITED STATES DEPARTMENT OF COMMERCE
United States Patent and Trademark Office
Address: COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, Virginia 22313-1450
www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/761,641	01/18/2001	Shunpei Yamazaki	740756-002249	6097	
22204	7590 07/02/2003				
	NIXON PEABODY, LLP			EXAMINER	
SUITE 800	SBORO DRIVE		BOOTH, RICHARD A		
MCLEAN, V	A 22102		ART UNIT	PAPER NUMBER	
•			2812	•	
			DATE MAILED: 07/02/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

		· IUIV			
	Application No.	Applicant(s)			
Office Action Cummen.	09/761,641	YAMAZAKI ET AL.			
Office Action Summary	Examiner	Art Unit			
	Richard A. Booth	2812			
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address			
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is tess than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period we Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status	6(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days all apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	ely filed s will be considered timely. the mailing date of this communication. O (35 U.S.C. § 133).			
1)⊠ Responsive to communication(s) filed on <u>29 A</u>	pril 2003				
<u></u>					
,	s action is non-final.	anantina on to the morte in			
3) Since this application is in condition for allowa closed in accordance with the practice under I	Ex parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.			
Disposition of Claims					
4) Claim(s) 1-14 is/are pending in the application					
4a) Of the above claim(s) is/are withdray	vn from consideration.				
5) Claim(s) is/are allowed.					
6)⊠ Claim(s) <u>1-14</u> is/are rejected.					
7) Claim(s) is/are objected to.					
8) Claim(s) are subject to restriction and/or	election requirement.				
Application Papers					
9) The specification is objected to by the Examine					
10) ☐ The drawing(s) filed on is/are: a) ☐ accept					
Applicant may not request that any objection to the					
11) The proposed drawing correction filed on is: a) approved b) disapproved by the Examiner.					
If approved, corrected drawings are required in reply to this Office action.					
12) The oath or declaration is objected to by the Ex	aminer.				
Priority under 35 U.S.C. §§ 119 and 120					
13) Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 119(a)-(d) or (f).			
a) ☐ All b) ☐ Some * c) ☐ None of:					
1. Certified copies of the priority documents	s have been received.				
2. Certified copies of the priority documents	s have been received in Applicati	on No			
3. Copies of the certified copies of the prior application from the International But * See the attached detailed Office action for a list	reau (PCT Rule 17.2(a)).				
14) Acknowledgment is made of a claim for domesti	·				
a) The translation of the foreign language pro	visional application has been rec	eived.			
Attachment(s)					
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s) 9	5) Notice of Informal I	(PTO-413) Paper No(s) Patent Application (PTO-152)			
S. Datast and Tradamad. Office					

Application/Control Number: 09/761,641

Art Unit: 2812

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claims 1-3, 6-8, and 11 are rejected under 35 U.S.C. 103(a) as being unpatentable over Silver, U.S. Patent 5,104,818 in view of Yamazaki, U.S. Patent 4,727,044.

Silver shows the invention substantially as claimed including a method of manufacturing a semiconductor device comprising: ion-doping an impurity element into a channel region, wherein said impurity element imparts p-type conductivity to said

Application/Control Number: 09/761,641

Art Unit: 2812

semiconductor film (see fig. 1C), wherein the concentration of said impurity element is 2 x 10¹⁷ atoms/cm³ after the step (see figs. 1c-1f and col. 2-lines 29-54).

Silver is applied as above but fails to expressly disclose the concentration of carbon, oxygen, and nitrogen of less than 3 x 10¹⁷ atoms/cm³.

Yamazaki discloses forming a semiconductor film so that the oxygen, carbon, and nitrogen concentrations in the film are all less than 5 x 10¹⁸ atoms/cm³ in order to obtain a large drain current (see col. 8-lines 3-23). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Silver so as to form the semiconductor film with low oxygen, carbon, and nitrogen concentration levels as specified by Yamazaki because this will produce a transistor with good electrical characteristics.

Regarding the doping gases being used, official notice was taken regarding this fact in the office action mailed 10-10-02, and therefore this limitation is taken to be admitted prior art.

Claims 4-5 rejected under 35 U.S.C. 103(a) as being unpatentable over Silver, U.S. Patent 5,104,818 in view of Yamazaki, U.S. Patent 4,727,044 as applied to claims 1-3, 6-8, and 11 above, and further in view of Zhang et al., U.S. Patent 5,904,509.

Silver and Yamazaki are applied as above but fail to expressly disclose performing implantation without mass separation and through an insulating film.

Zhang et al. discloses performing plasma doping without mass separation and implanting these ions into a semiconductor film through an insulating film (see col. 8-line Application/Control Number: 09/761,641

Art Unit: 2812

59 to col. 9-line 2). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Silver and Yamazaki so as to conduct the implantation using plasma doping through an insulating film since plasma doping is shown to be a suitable method of injecting ions into a semiconductor and because it is well known to use screen oxides during implantation in order to reduce damage to the substrate.

Claims 9-10 and 12-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Silver, U.S. Patent 5,104,818 in view of Yamazaki, U.S. Patent 4,727,044 as applied to claims 1-3, 6-8, and 11 above, and further in view of Miyasaka, U.S. Patent 6,455,360

Silver and Yamazaki are applied as above but fail to expressly disclose wherein an impurity element imparting p-type conductivity is conducted with a gas of diborane diluted with hydrogen from 0.5% to either 1 or 5 percent so that the concentration of hydrogen is 1×10^{19} atoms/cm³ or less.

Miyasaka discloses performing a doping step using diborane diluted with hydrogen at a concentration of 0.1 to 10% (see col. 22-lines 37-41). In view of this disclosure, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify the process of Zhang so as to include a diborane gas diluted with hydrogen because Miyasaka shows this to be a suitable combination to form doped region in thin film structures.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Richard A. Booth whose telephone number is 308-3446. The examiner can normally be reached on Monday-Thursday from 7:30-6:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on 308-3325. The fax phone numbers for the organization where this application or proceeding is assigned are 308-7724 for regular communications and 308-7724 for After Final communications.

Art Unit: 2812

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 308-1782.

Richard A. Booth Primary Examiner Art Unit 2812

June 30, 2003